

N-channel 40 V 2.1 mΩ standard level MOSFET 22 February 2013 P

**Product data sheet** 

## 1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 3. Applications

- DC-to-DC convertors
- Load switching
- Motor control
- Server power supplies

## 4. Quick reference data

Table 1. C	uick reference data	1					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 3</u> ; <u>Fig. 1</u>		-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	306	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	[1]	-	1.75	2.1	mΩ
Dynamic ch	aracteristics						
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 80 A; V <sub>DS</sub> = 20 V; Fig. 14; Fig. 15		-	25	-	nC

[1] Measured 3 mm from package.



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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G L F A
mb	D	drain		mbb076 S
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMN2R2-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78					

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN2R2-40PS	PSMN2R2-40PS

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	40	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	40	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	-	100	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 3</u> ; <u>Fig. 1</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3	-	1122	А

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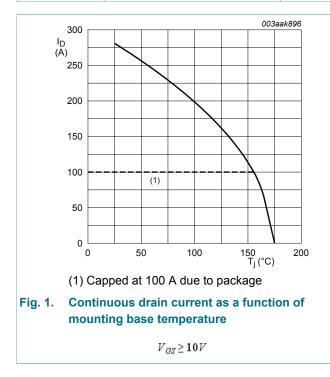
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Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	306	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$	-	1122	А
Avalanche i	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{split} V_{GS} &= 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^\circ\text{C};  \text{I}_\text{D} = 100 \text{ A}; \\ V_{sup} &\leq 40 \text{ V}; \text{ unclamped};  \text{R}_{\text{GS}} = 50  \Omega \end{split}$	-	1.24	J



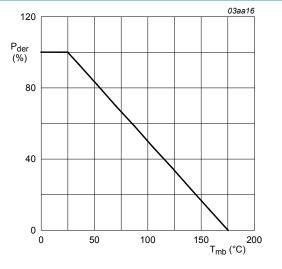


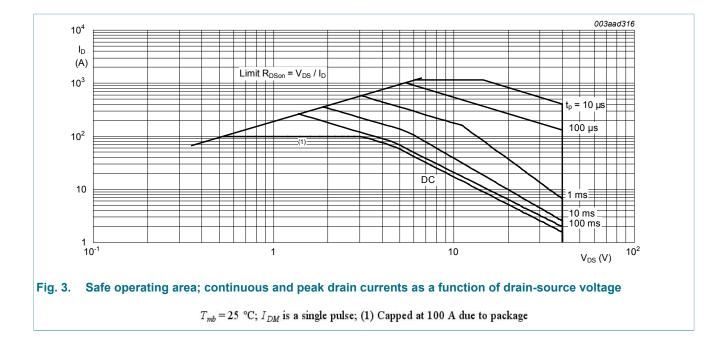
Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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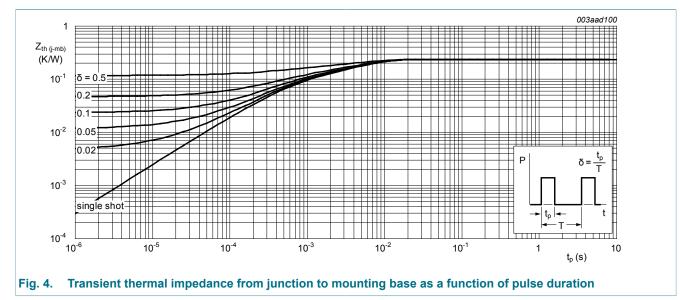
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## 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	0.25	0.5	K/W



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## **10. Characteristics**

#### Table 7. **Characteristics** Tested to JEDEC standards where applicable. **Symbol** Parameter **Conditions** Min Тур Max Unit Static characteristics drain-source I<sub>D</sub> = 250 μA; V<sub>GS</sub> = 0 V; T<sub>i</sub> = -55 °C V 36 V<sub>(BR)DSS</sub> \_ breakdown voltage I<sub>D</sub> = 250 μA; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C V 40 \_ - $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = -55 \text{ °C};$ gate-source threshold 4.6 V V<sub>GS(th)</sub> -\_ voltage Fig. 10 I<sub>D</sub> = 1 mA; V<sub>DS</sub> = V<sub>GS</sub>; T<sub>i</sub> = 175 °C; v 1 \_ \_ Fig. 10 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = 25 \text{ °C};$ 2 3 4 V Fig. 11; Fig. 10 V<sub>DS</sub> = 40 V; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C drain leakage current 10 μA \_ IDSS -V<sub>DS</sub> = 40 V; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 125 °C 200 uА -\_ V<sub>GS</sub> = 20 V; V<sub>DS</sub> = 0 V; T<sub>i</sub> = 25 °C 100 nA gate leakage current I<sub>GSS</sub> \_ -V<sub>GS</sub> = -20 V; V<sub>DS</sub> = 0 V; T<sub>i</sub> = 25 °C nA 100 - $V_{GS}$ = 10 V; I<sub>D</sub> = 25 A; T<sub>j</sub> = 100 °C; drain-source on-state \_ 2.4 2.85 mΩ R<sub>DSon</sub> resistance Fig. 12; Fig. 13 V<sub>GS</sub> = 10 V; I<sub>D</sub> = 25 A; T<sub>i</sub> = 175 °C; 3.25 3.9 mΩ -Fig. 12; Fig. 13 V<sub>GS</sub> = 10 V; I<sub>D</sub> = 25 A; T<sub>i</sub> = 25 °C; 1.75 2.1 mΩ [1] -Fig. 12 $R_{G}$ internal gate f = 1 MHz\_ 1 \_ Ω resistance (AC) **Dynamic characteristics** $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ nC total gate charge 110 Q<sub>G(tot)</sub> \_ \_ $I_D = 80 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ 130 nC -\_ Fig. 14; Fig. 15 $\mathsf{Q}_{\mathsf{GS}}$ gate-source charge 42 nC -\_ pre-threshold gate-24 nC Q<sub>GS(th)</sub> \_ \_ source charge post-threshold gate-18 nC Q<sub>GS(th-pl)</sub> \_ \_ source charge gate-drain charge 25 nC $Q_{GD}$ -\_ V<sub>GS(pl)</sub> gate-source plateau I<sub>D</sub> = 80 A; V<sub>DS</sub> = 20 V; <u>Fig. 14</u>; <u>Fig. 15</u> \_ 4.95 -V voltage input capacitance V<sub>DS</sub> = 20 V; V<sub>GS</sub> = 0 V; f = 1 MHz; Ciss 8423 pF \_ \_

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 $C_{\text{oss}}$ 

T<sub>i</sub> = 25 °C; <u>Fig. 16</u>

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-

output capacitance

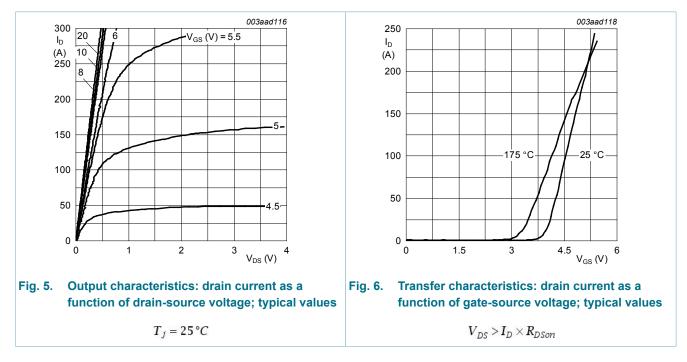
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C <sub>rss</sub>	reverse transfer capacitance			-	814	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; R <sub>L</sub> = 0.25 Ω; V <sub>GS</sub> = 10 V;		-	33.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$		-	40.4	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	66.6	-	ns
t <sub>f</sub>	fall time	-		-	25.2	-	ns
Source-drain	diode					1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{S}/dt = -100 A/µs; V_{\rm GS} = 0 V; V_{\rm DS} = 20 V		-	53.7	-	ns
Q <sub>r</sub>	recovered charge	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	80.75	-	nC

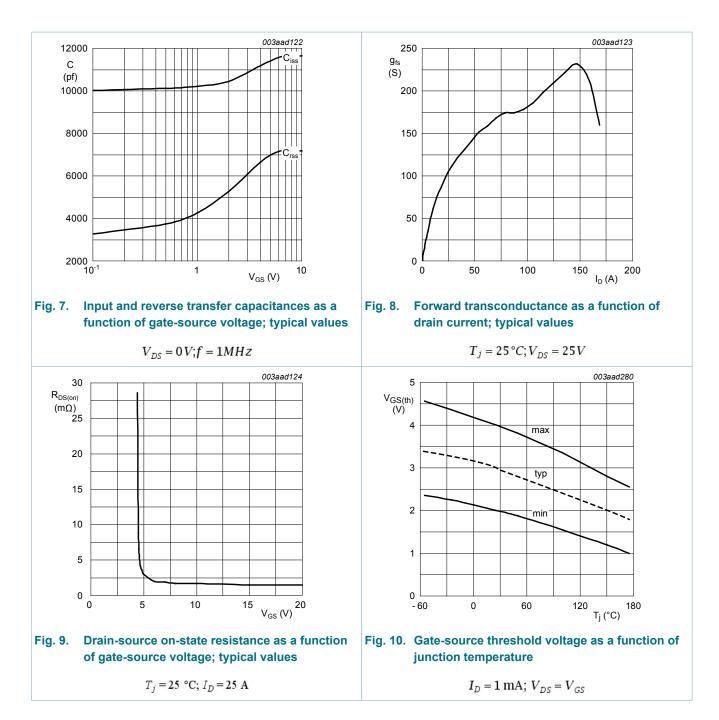
[1] Measured 3 mm from package.



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5.5

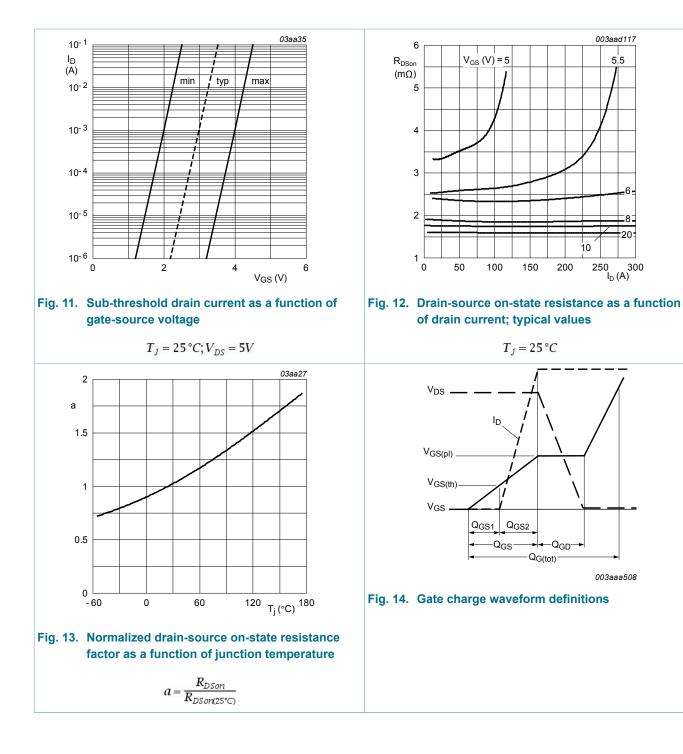
20

250 300 I<sub>D</sub> (A)

003aaa508

10

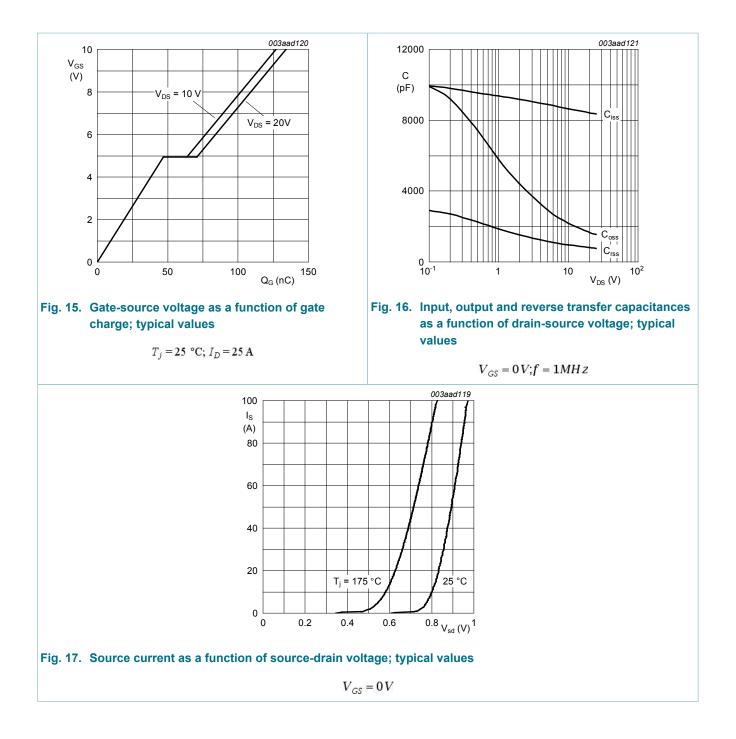
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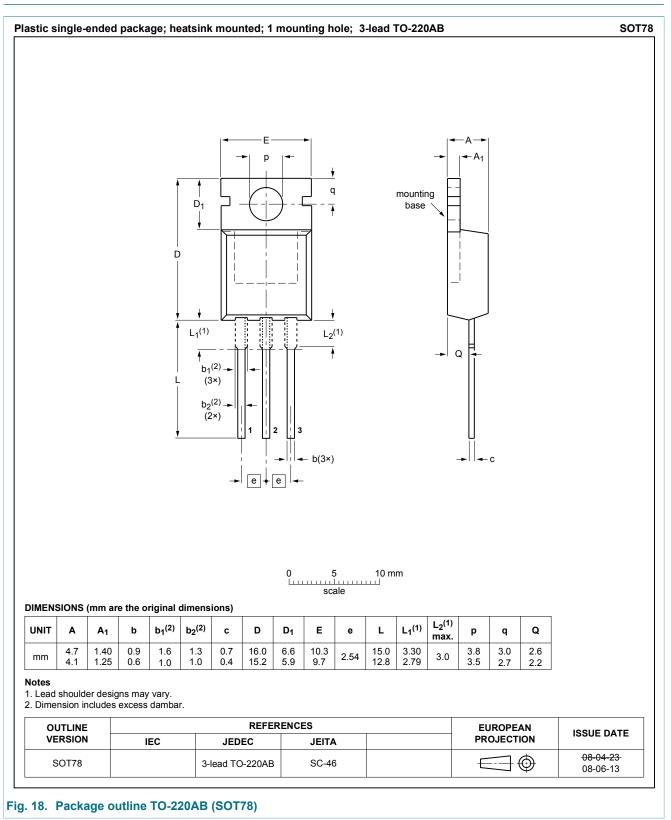
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## 11. Package outline



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**Product data sheet** 

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## 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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